



Attorney Docket No. 0756-2332

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:) Group Art Unit: 2825
Takeshi FUKADA et al.) Examiner: L. Malsawma
Serial No. 09/904,906) <u>CERTIFICATE OF MAILING</u>
Filed: July 16, 2001) I hereby certify that this correspondence is
For: GLASS SUBSTRATE ASSEMBLY,) being deposited with the United States Postal
SEMICONDUCTOR DEVICE AND) Service with sufficient postage as First Class
METHOD OF HEAT-TREATING) Mail in an envelope addressed to:
GLASS SUBSTRATE) Commissioner for Patents, P.O. Box 1450,
) Alexandria, VA 22313-1450, on
) <u>3.31.2004</u>
) <u>Asile M. Stamps</u>

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

U.S. Patent Nos. 5,308,998; 5,913,112, and 5,962,870 are in the family of JP 05-114724.

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be

required now or hereafter, or credit any overpayment to Deposit Account No. 50-2280.
A duplicate copy of this sheet is attached.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	09/904,906
Filing Date	July 16, 2001
First Named Inventor	Takeshi FUKADA et al.
Group Art Unit	2825
Examiner Name	L. Malsawma
Attorney Docket Number	0756-2332

Sheet 1 of 2

U.S. PATENT DOCUMENTS

Examiner Initials [*]	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		4,416,952		Nishizawa et al.	11/22/1983	
		4,727,044		Yamazaki	02/23/1988	
		5,147,826		Liu et al.	09/15/1992	
		5,250,444		Khan et al.	10/05/1993	
		5,270,263		Kim et al.	12/14/1993	
		5,275,851		Fonash et al.	01/04/1994	
		5,278,093		Yonehara	01/11/1994	
		5,306,651		Masumo et al.	04/26/1994	
		5,308,998		Yamazaki et al.	05/03/1994	
		5,323,042		Matsumoto	06/21/1994	
		5,352,291		Zhang et al.	10/04/1994	
		5,359,219		Hwang	10/25/1994	
		5,488,000		Zhang et al.	01/30/1996	
		5,521,107		Yamazaki et al.	05/28/1996	
		5,532,953		Ruesch et al.	07/02/1996	
		5,552,624		Skotnicki et al.	09/03/1996	
		5,849,043		Zhang et al.	12/15/1998	
		5,913,112		Yamazaki et al.	06/15/1999	
		5,962,870		Yamazaki et al.	10/05/1999	
		6,013,928		Yamazaki et al.	01/11/2000	
		6,268,631		Fukada et al.	07/31/2001	

FOREIGN PATENT DOCUMENTS

Examiner Initials [*]	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		JP	01-144139			06/06/1989		AB
		JP	03-022540			01/30/1991		FULL
		JP	03-024736			02/01/1991		AB

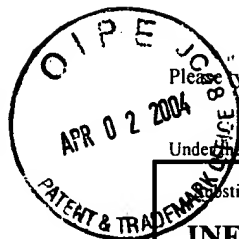
Examiner Signature	Date Considered
--------------------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.



Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	09/904,906
				Filing Date	July 16, 2001
				First Named Inventor	Takeshi FUKADA et al.
				Group Art Unit	2825
				Examiner Name	L. Malsawma
Sheet	2	of	2	Attorney Docket Number	0756-2332

FOREIGN PATENT DOCUMENTS								
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		JP	03-034434			02/14/1991		AB
		JP	03-181119			08/07/1991		AB
		JP	03-218640			09/26/1991		AB
		JP	03-227525			10/08/1991		AB
		JP	03-265143			11/26/1991		AB
		JP	03-289129			12/19/1991		AB
		JP	03-293719			12/25/1991		AB
		JP	05-067635			03/19/1993		FULL
		JP	05-114724			05/07/1993		AB
		JP	05-152325			06/18/1993		AB
		JP	07-131034			05/19/1995		AB
		JP	56-023748			03/06/1981		AB
		JP	04-144139			05/18/1992		AB

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Gang Liu et al., <i>Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing</i> , Appl. Phys. Lett., Vol. 62, No. 20, Pages 2554-2556, May 17, 1993.	
		Gang Liu et al., <i>Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing</i> , Appl. Phys. Lett., Vol. 55, No. 7, Pages 660-662, August 14, 1989.	
		C. Hayzelden et al., <i>In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon</i> , Appl. Phys. Lett., Vol. 60, No. 2, Pages 225-227, January 13, 1992.	
		<i>Applied Technology of High Purity Silica</i> , Pages 131-133, March 1, 1991.	
		R. Kakkad et al., <i>Crystallized Si Films by Low-Temperature Rapid Thermal Annealing of Amorphous Silicon</i> , J. Appl. Phys., Vol. 65, Pages 2069-2072, March 1, 1989.	
		R. Kakkad et al., <i>Low Temperature Selective Crystallization of Amorphous Silicon</i> , Journal of Non-Crystalline Solids, Vol. 115, Pages 66-68, August 1, 1989.	
		A.V. Dvurechenskii et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol., Vol. 95, Pages 635-640, January 1, 1986.	
		T. Hempel et al., <i>Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films</i> , Solid State Communications, Vol. 85, No. 11, Pages 921-924, March 1, 1993.	
		E. Korin et al., <i>Crystallization of Amorphous Silicon Films Using a Multistep Thermal Annealing Process</i> , Thin Solid Films, Vol. 167, Pages 101-106, January 1, 1998	

Examiner Signature		Date Considered	
-----------------------	--	--------------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.